

FQS4901

N-Channel QFET® MOSFET

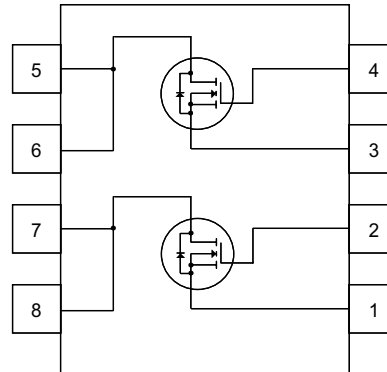
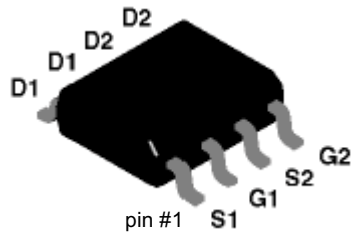
400 V, 0.45 A, 4.2 Ω

Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor®'s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- 0.45 A, 400 V, $R_{DS(on)}=4.2 \Omega(\text{Max.})@V_{GS}=10 \text{ V}, I_D=0.225 \text{ A}$
- Low Gate Charge (Typ. 5.8 nC)
- Low C_{rss} (Typ. 5 pF)
- 100% Avalanche Tested



Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQS4901	Unit
V_{DSS}	Drain-Source Voltage	400	V
I_D	Drain Current - Continuous ($T_A = 25^\circ\text{C}$) - Continuous ($T_A = 70^\circ\text{C}$)	0.45	A
		0.285	A
I_{DM}	Drain Current - Pulsed (Note 1)	1.8	A
V_{GSS}	Gate-Source Voltage	± 25	V
dv/dt	Peak Diode Recovery dv/dt (Note 2)	4.5	V/ns
P_D	Power Dissipation ($T_A = 25^\circ\text{C}$) ($T_A = 70^\circ\text{C}$)	2.0	W
		1.3	W
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	62.5	$^\circ\text{C/W}$

Electrical Characteristics T_A = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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Off Characteristics

BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	400	--	--	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	--	0.42	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 400 V, V _{GS} = 0 V	--	--	1	μA
		V _{DS} = 320 V, T _C = 125°C	--	--	10	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 25 V, V _{DS} = 0 V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -25 V, V _{DS} = 0 V	--	--	-100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	2.0	--	4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 0.225 A	--	3.2	4.2	Ω
g _{FS}	Forward Transconductance	V _{DS} = 35 V, I _D = 0.225 A (Note 3)	--	0.283	--	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz	--	160	210	pF
C _{oss}	Output Capacitance		--	30	40	pF
C _{rss}	Reverse Transfer Capacitance		--	5	6.5	pF

Switching Characteristics

t _{d(on)}	Turn-On Delay Time	V _{DD} = 200 V, I _D = 0.45 A, R _G = 25 Ω (Note 3,4)	--	5	20	ns
t _r	Turn-On Rise Time		--	20	50	ns
t _{d(off)}	Turn-Off Delay Time		--	20	50	ns
t _f	Turn-Off Fall Time		--	35	80	ns
Q _g	Total Gate Charge	V _{DS} = 320 V, I _D = 0.45 A, V _{GS} = 10 V (Note 3,4)	--	5.8	7.5	nC
Q _{gs}	Gate-Source Charge		--	0.53	--	nC
Q _{gd}	Gate-Drain Charge		--	3.22	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current	--	--	0.45	A	
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	1.8	A	
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 0.45 A	--	--	1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 0.45 A, di _F / dt = 100 A/μs (Note 3)	--	86	--	ns
Q _{rr}	Reverse Recovery Charge		--	0.15	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. I_{SD} ≤ 0.45A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
3. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%
4. Essentially independent of operating temperature

Typical Characteristics

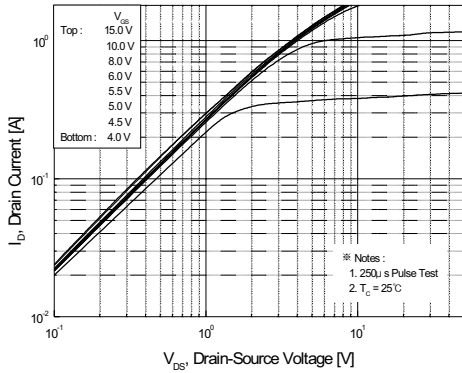


Figure 1. On-Region Characteristics

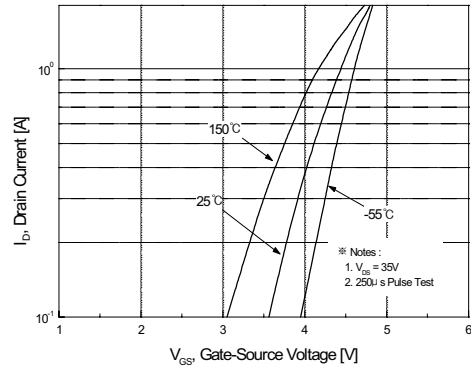


Figure 2. Transfer Characteristics

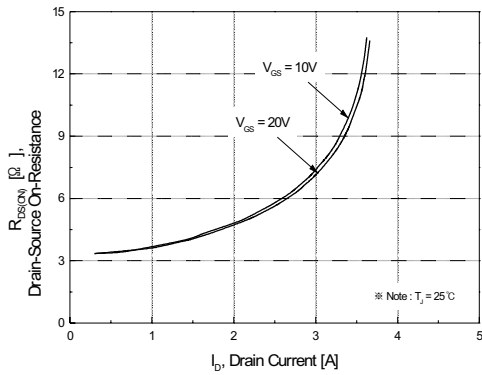


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

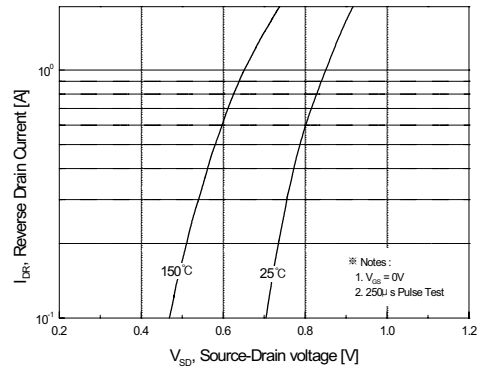


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

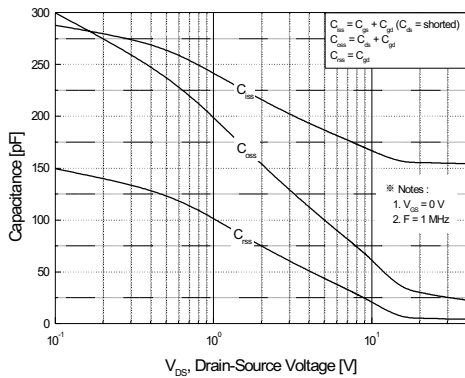


Figure 5. Capacitance Characteristics

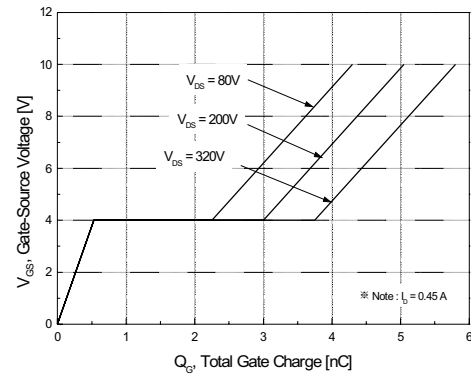


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

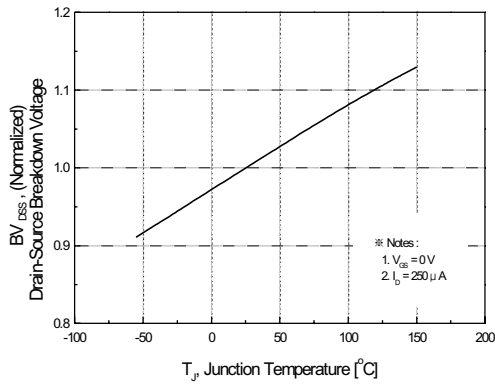


Figure 7. Breakdown Voltage Variation vs. Temperature

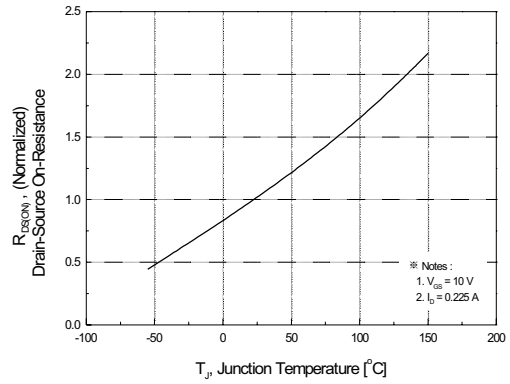


Figure 8. On-Resistance Variation vs. Temperature

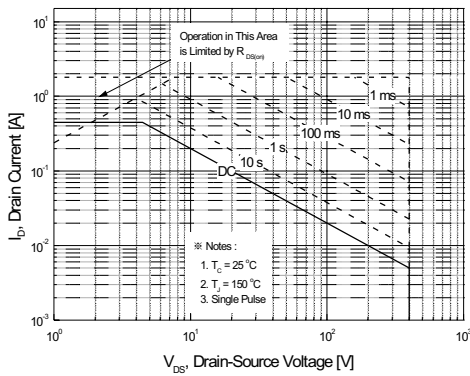


Figure 9. Maximum Safe Operating Area

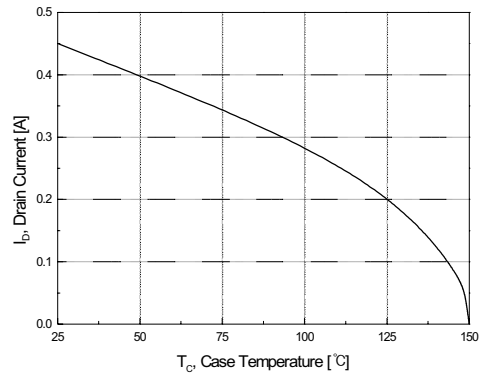


Figure 10. Maximum Drain Current vs. Case Temperature

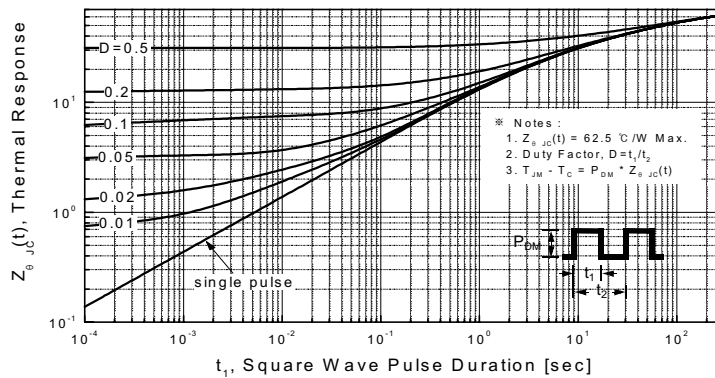
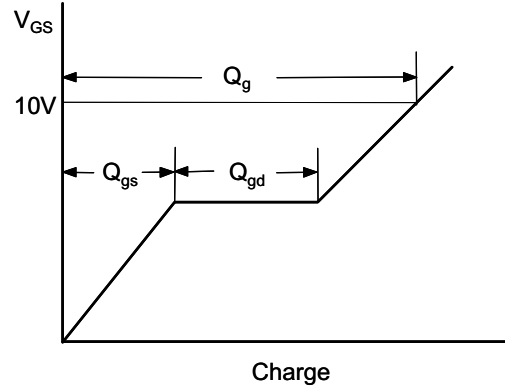
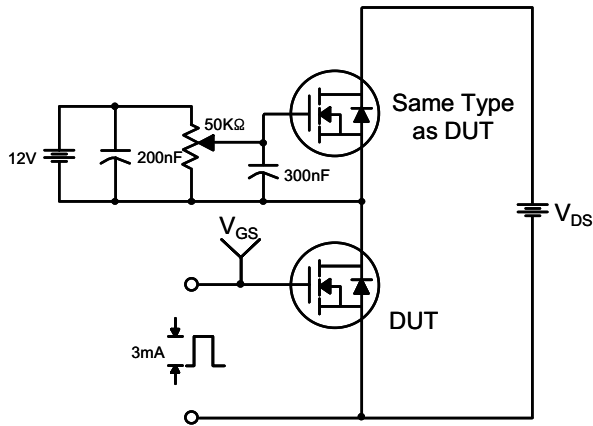
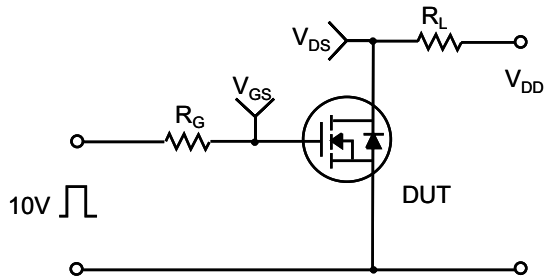


Figure 11. Transient Thermal Response Curve

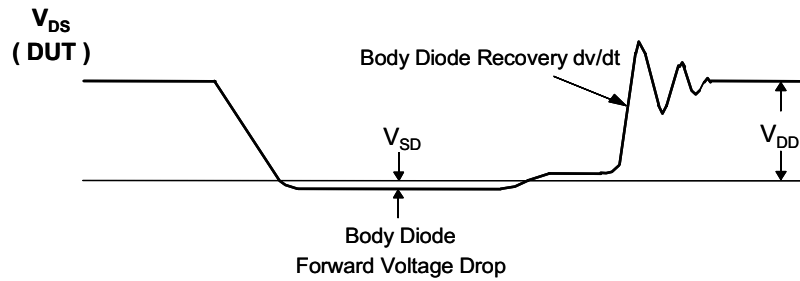
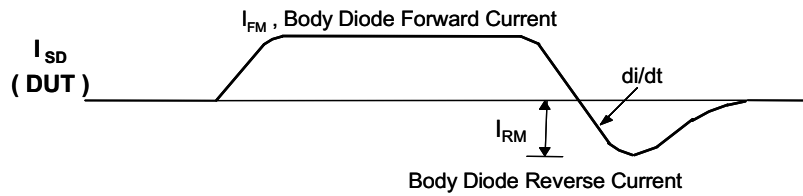
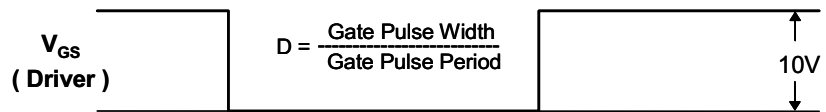
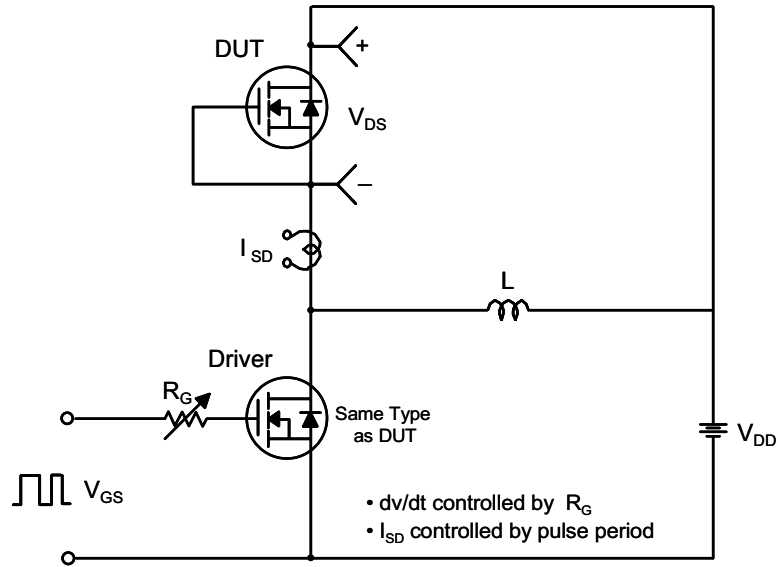
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

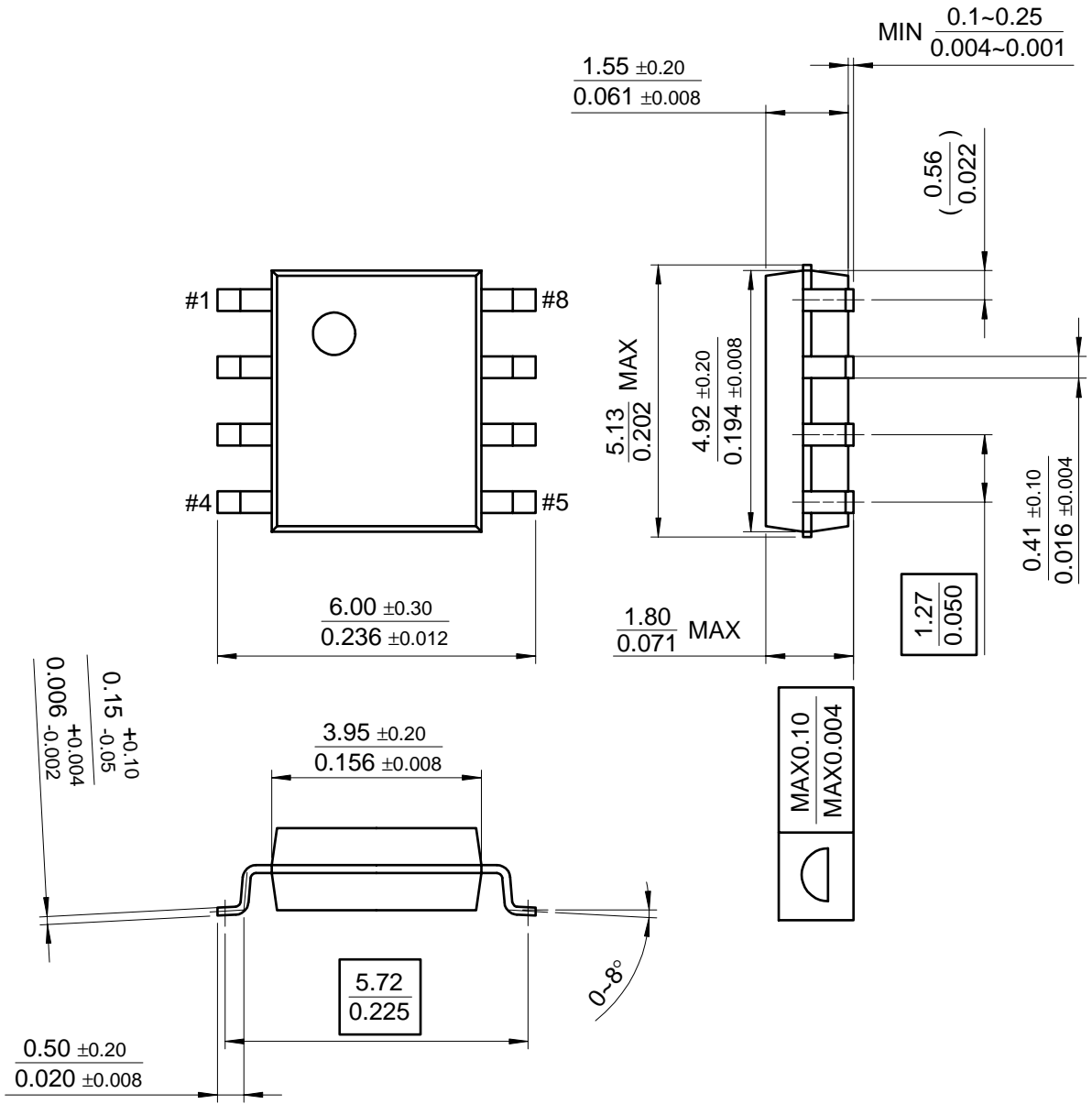


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimensions

8SOP





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